Monolithic Microwave Integrated GaAs FET Oscillators

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The analysis by means of three-port S-parameters shows that larger output power can be obtained from GaAa MESFET oscillator at their source ports rather than at their drains. An output power of 40 mW was measured at 8.2 GHz on a finished monolithic oscillator with 15% efficiency and 300 µm gate-width.

❑ Return to main document.